

08/08/2019

EE5311

MODULE - 1: THE TRANSISTOR

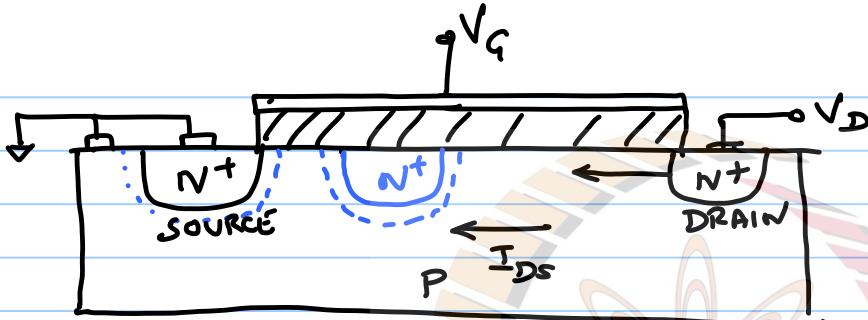
SHORT CHANNEL EFFECTS (SCE)

1) CHANNEL LENGTH MODULATION (CLM) $\rightarrow \frac{\Delta L}{L} = \lambda V_{DS}$

$$I_D = \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$

2) VELOCITY SATURATION:

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$V_{DD} \downarrow$ WITH TECH

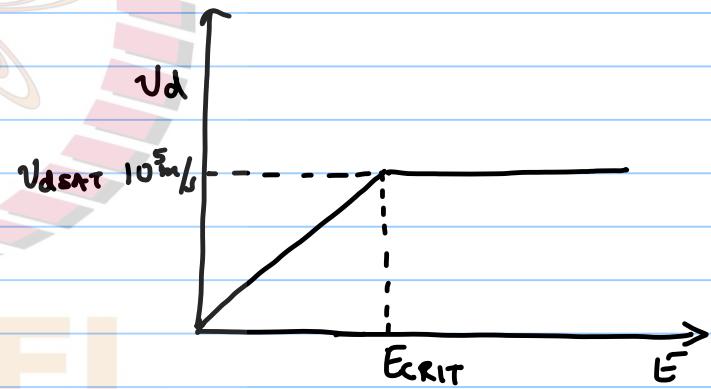
$$E = \frac{V_{DS}}{L}$$

$$v_d = \text{drift vel} \leq 10^5 \text{ m/s}$$

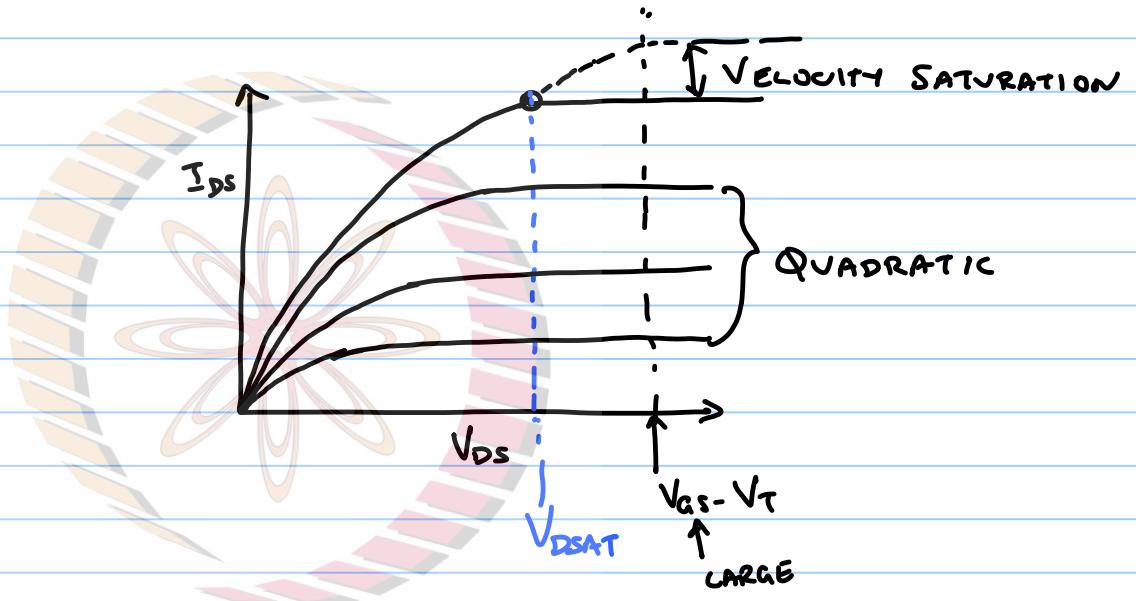
$$v_d = \mu_n E$$

$$v_{DSAT} = \mu_n \cdot \frac{V_{DSAT}}{L}$$

$$\therefore V_{DSAT} = \frac{v_{DSAT} \cdot L}{\mu_n}$$



$V_{GS} \rightarrow$ SMALL ($>V_T$)
 $V_{GS} \rightarrow$ LARGE

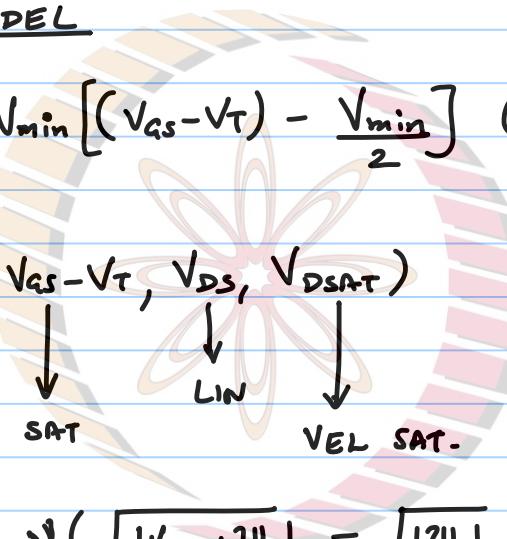


$$I_D = \begin{cases} 0 & V_{GS} < V_T \\ \mu n C_o x \frac{W}{L} V_{DS} \left[(V_{GS} - V_T) - \frac{V_{DS}}{2} \right] & V_{DS} \leq V_{GS} - V_T \rightarrow \text{LINEAR (TRIODE)} \\ \frac{1}{2} \mu n C_o x \frac{W}{L} (V_{GS} - V_T)^2 & V_{DS} = V_{GS} - V_T \rightarrow (\text{SATURATION}) \\ \mu n C_o x \frac{W}{L} V_{DSAT} \left[(V_{GS} - V_T) - \frac{V_{DSAT}}{2} \right] & V_{DSAT} < V_{GS} - V_T \quad (\text{VEL SAT}) \end{cases}$$

UNIFIED CURRENT MODEL

$$I_D = \frac{\mu_n C_{ox}}{K_n} \frac{W}{L} V_{min} \left[(V_{GS} - V_T) - \frac{V_{min}}{2} \right] (1 + \lambda V_{DS}) \quad \boxed{\frac{\Delta L}{L}}$$

$$V_{min} = \min (V_{GS} - V_T, V_{DS}, V_{DSAT})$$



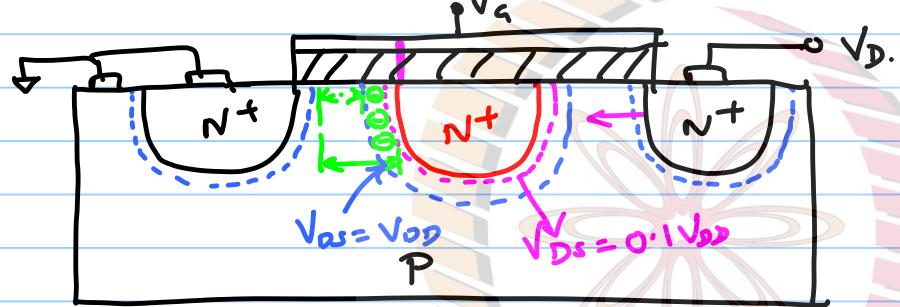
 SAT LIN VEL SAT.

$$V_{TH0} = V_{TH0} + \gamma (\sqrt{|V_{SB} + \psi_s|} - \sqrt{|\psi_s|})$$

5 PARAMETERS : $(K_n^i, V_{DSAT}, \lambda, V_{TH0}, \gamma)$ ← LEVEL 1 SPICE MODEL
 (TECHNOLOGY PARAMETERS)

$$K_n^i = \mu_n C_{ox} = \mu_n \frac{\epsilon_{ox}}{t_{ox}}$$

DRAIN INDUCED BARRIER LOWERING (DIBL)

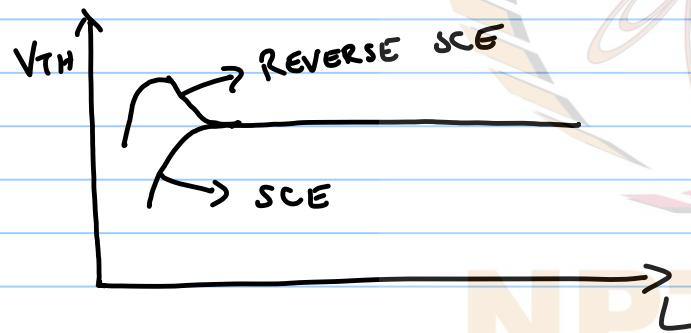
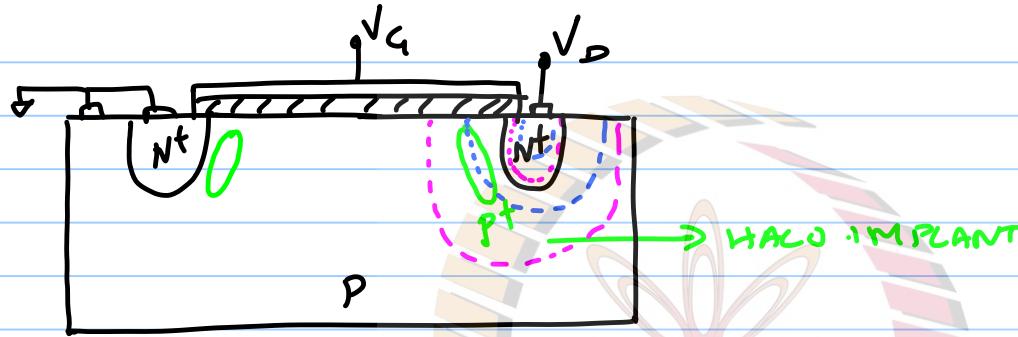


$$V_{DS1} = 0.1 V_{DD} \rightarrow V_{TH} = V_{TLIN}$$

$$V_{DS2} = V_{DD} \rightarrow V_{TH} = V_{TSAT}$$

$$\eta = DIBL = \frac{V_{TLIN} - V_{TSAT}}{(V_{DD} - 0.1 V_{DD})}$$

$$V_{TH} = V_{TH0} + \gamma (\sqrt{|V_{SB} + \Psi_S|} - \sqrt{|\Psi_S|}) - \eta V_{DS}$$



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